P.n Junction: If a f type and an type * If a donar inferrities (n'type) care introduced into one side and acceptor (Ptype) into the other side of a single crystal of a semiconductor then a p-n junction is formed. Pu junction diode conducts only in one Cathode direction. The resistance un the other Prejuveton Diode direction is very high thus, unable to conduct.

Depative acceptor ion poles (2) , electrons Donai ion holesty n selectrons

(majority

Carrier)

(majority

Carrier)

(majority

Carrier)

(minority

Carrier) magative edections miority The situation after forming of Pu Junetion elections (pside) holes (fowards n side)) The holes of & type diffuse to the right side across the junition and the elections of in type diffuse towards left side of the junction 2) The diffusion of carriers occurs due to difference in concentration of Carriers each side of the junction 3) Thus, both electrons & Groles rentralizes each offrer. 4) But, The cons (which are immobile) are uncompensated near the junction

الله ومعلولة الأور 1831 in all work The unneutralized ions in the reighborhood of the junction are referred to as un covered charges. 6) The region containing the uncompensated acceptor and donar ions is called Depletion region. That is there es a depletion of mobile charges (holes and free elections) in this region. The electric field between the acceptor & donar ions is called barrier. The additional broles trying to diffuse into Novepion are refelled by uncompensated the charge of donar ions and the



additional electrons trying to diffuse unto Pregion are réfelled by uncompensated - ne charges con acceptos ions. 8) Thus, barrier is formed whose width is nearly 0'5 um and is also, known as space charge region. (D 0 (D) (D) (D) Space Charge or Depletion wilth Bias -> refers to application of an external Voltage across the terminals of the device.



In the absence of bras or When bias = 0) i'e VD zo Volt The net flow of one direction Thus current is Electronis